



Product Specification

DESCRIPTION

The GLF1501 load Switch is a fully integrated 3 A NMOS load switch with I_QSmart^{TM} advanced technology. The device is targeted for the mobile computing and data storage markets as a high performance, low-cost solution for load switch applications.

The GLF1501 has a constant low on-resistance of 52 m Ω at room temperature. The fixed rise time helps prevent undesirable inrush current when turned on and the internal EN pin pulldown resistor ensures the device remains in the shutdown mode when disabled. In shutdown mode the GLF1501 draws only 6 nA typical at 3.6 V input supply voltage.

The GLF1501 features a reverse current blocking protection. When the GLF1501 is disabled, it prevents reverse current flowing from the output to the input source.

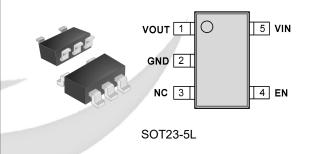
FEATURES

- Supply Voltage Range: 0.85 V to 3.6 V
- Low Ron: 52 mΩ Typ at Supply Voltage Range
- I_{OUT} Max: 3 A
- Ultra-Low IQ:
 - 50 nA Typ at 0.85 V_{IN}
 - o 60 nA Typ at 1.0 V_{IN}
 - 120 nA Typ at 1.5 V_{IN}
- Integrated Slew Rate Control Driver
- Reverse Current Blocking Protection When Disabled
- Internal EN Pull-Down Resistor
- Integrated Output Discharge Switch
- HBM: 4 kV, CDM: 2 kV

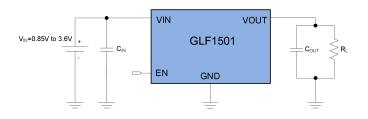
APPLICATIONS

- Low Power Subsystems
- Wearables
- Data Storage

PACKAGE



APPLICATION DIAGRAM



ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	R _{ON} (Typ) at Vin Range	Output Discharge	EN Activity
GLF1501-T1G7	FC	52 mΩ	85 Ω	High

FUNCTIONAL BLOCK DIAGRAM

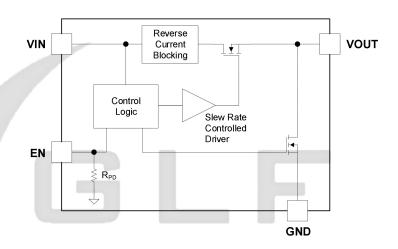


Figure 1. Functional Block Diagram

PIN CONFIGURATION

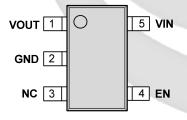


Figure 2. SOT23-5L

PIN DEFINITION

Pin#	Name	Description
1	V _{OUT}	Switch Output
2	GND	Ground
3	NC	No connection
4	EN	Enable to control the switch
5	V _{IN}	Switch Input. Supply Voltage for IC



ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit
V_{IN}	V _{IN} , V _{OUT} , V _{EN} to GND	-0.3	4	V
l _{out}	Maximum Continuous Switch Current		3	Α
P _D	Power Dissipation at T _A = 25°C		1	W
T _{STG}	Storage Junction Temperature	-65	150	°C
T _A	Operating Temperature Range	-40	85	°C
θ_{JC}	Thermal Resistance, Junction to Case		90	°C/W
θја	Thermal Resistance, Junction to Ambient (Measured using 2S2P JEDEC std. PCB.)		180	°C/W

ESD Ratings

Symbol		Parameter					
HBM	Electrostatic Discharge Canability	Human Body Model, JESD22-A114	4	kV			
CDM	Electrostatic Discharge Capability	Charged Device Model, JESD22-C101	2	K.V			

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
V _{IN}	Supply Voltage	0.85	3.6	V
T _A	Ambient Operating Temperature	-40	+85	°C

ELECTRICAL CHARACTERISTICS

 V_{IN} = 0.85 V to 3.6 V and T_A = 25 °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Ma x.	Units				
Basic Ope	ration		•							
		EN = Enable, I _{OUT} = 0 mA, V _{IN} = 0.85 V		50						
		EN = Enable, I _{OUT} = 0 mA, V _{IN} = 1.0 V		60		nA				
		EN = Enable, I _{OUT} = 0 mA, V _{IN} = 1.5 V		120						
I.	Quiescent Current	EN = Enable, I _{OUT} = 0 mA, V _{IN} = 2.5 V		7						
lα	Quiescent Current	EN = Enable, I _{OUT} = 0 mA, V _{IN} = 3.0 V		16						
		EN = Enable, I _{OUT} = 0 mA, V _{IN} = 3.3 V		22		μA				
		EN = Enable, I _{OUT} = 0 mA, V _{IN} = 3.6 V		30						
		EN = Enable, I_{OUT} = 0 mA, V_{IN} = 3.6 V, Ta = 85 °C		46						
		EN = Disable, I _{OUT} = 0 mA, V _{IN} = 0.85 V		4						
		EN = Disable, I _{OUT} = 0 mA, V _{IN} = 1.0 V		4						
		EN = Disable, I _{OUT} = 0 mA, V _{IN} = 1.2 V		4						
	Chutdown Current	EN = Disable, I _{OUT} = 0 mA, V _{IN} = 2.5 V		4		π Λ				
I_{SD}	Shutdown Current	EN = Disable, I _{OUT} = 0 mA, V _{IN} = 3.0 V		5		nA				
		EN = Disable, I _{OUT} = 0 mA, V _{IN} = 3.3 V		5						
		EN = Disable, I _{OUT} = 0 mA, V _{IN} = 3.6 V		6	10					
A		EN = Disable, I_{OUT} = 0 mA, V_{IN} = 3.6 V, Ta = 85 °C		820	950	3				
Б	On Registance	V _{IN} = 0.85 V to 3.6 V Ta = 25 °C		52	63	m0				
R _{ON}	On-Resistance	I _{OUT} = 300 mA Ta = 85 °C		62	71	mΩ				
\/	CN Input Lagis High Voltage	V _{IN} = 0.85 V to 1.5 V	0.8			V				
V_{IH}	EN Input Logic High Voltage	V _{IN} = 1.5 V to 3.6 V	1.1			V				
\/	CN Input Logic Low Voltage	V _{IN} = 0.85 V to 1.5 V			0.2	V				
V_{IL}	EN Input Logic Low Voltage	V _{IN} = 1.5 V 3.6 V	/		0.5	V				
R _{EN}	EN pull down resistance	Internal Resistance		10		МΩ				
R _{DSC}	Output Discharge Resistance (1)	EN = GND		85		Ω				

Notes: 1. Output discharge path is disabled when main switch is off.

ELECTRICAL CHARACTERISTICS

 V_{IN} = 0.85 V to 3.6 V and T_A = 25 °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Switching	Characteristics (2)					
		V _{IN} = 0.85 V		2200		
4	Turn-On Delay	V _{IN} = 1.2 V		300		
t _{dON}	R_{OUT} = 150 Ω, C_{OUT} = 0.1 μF	V _{IN} = 3.3 V		145		
		V _{IN} = 3.6 V		125		
		V _{IN} = 0.85 V		3250		
	V_{OUT} Rise Time R_{OUT} = 150 Ω, C_{OUT} = 0.1 μF	V _{IN} = 1.2 V		500		
t _R		V _{IN} = 3.3 V		400		
		V _{IN} = 3.6 V		390		
		V _{IN} = 0.85 V		50		μs
	Turn-Off Delay	V _{IN} = 1.2 V		5		
t _{dOFF}	$R_{OUT} = 150 \Omega, C_{OUT} = 0.1 \mu F$	V _{IN} = 3.3 V		1		
		V _{IN} = 3.6 V		0.6		
		V _{IN} = 0.85 V		25		
t⊧	V_{OUT} Fall Time R_{OUT} = 150 Ω, C_{OUT} = 0.1 μF	V _{IN} = 1.2 V		17		
		V _{IN} = 3.3 V		12		
A	INI	V _{IN} = 3.6 V	\bigcirc	11	Eh	<

Notes: 2. By design; characterized, not production tested. $t_{ON} = t_{dON} + t_{R}$, $t_{OFF} = t_{dOFF} + t_{F}$

TIMING DIAGRAM

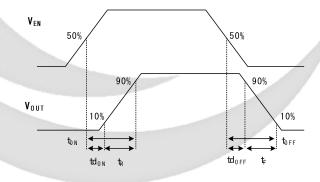


Figure 3. Timing Diagram

TYPICAL PERFORMANCE CHARACTERISTICS

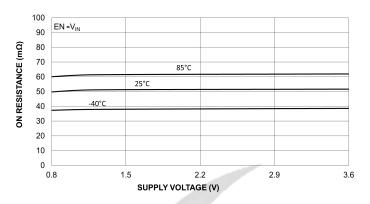


Figure 4. On-Resistance vs. Supply Voltage

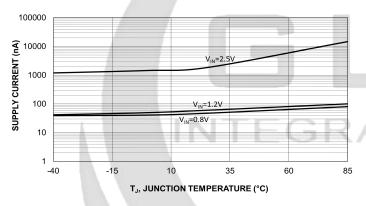


Figure 6. On-Resistance vs. Supply Voltage

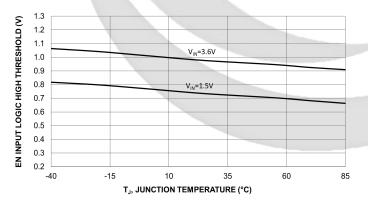


Figure 8. EN Input Logic High Threshold Vs. Temperature

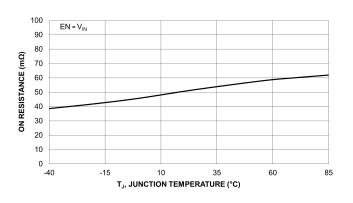


Figure 5. On-Resistance vs. Temperature

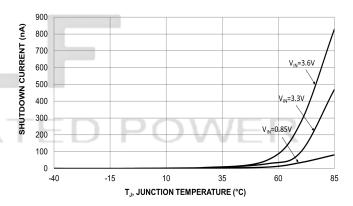


Figure 7. Shutdown Current vs. Supply Voltage

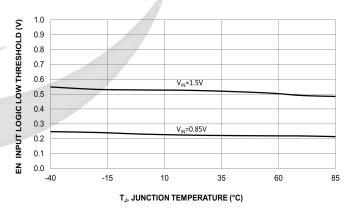


Figure 9. EN Input Logic Low Threshold Vs. Temperature

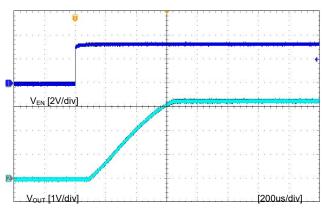


Figure 10. Turn-On Response $V_{\text{IN}} = 3.3 \text{ V, } C_{\text{OUT}} = 0.1 \text{ uF, } R_{\text{L}} = 150 \text{ }\Omega$

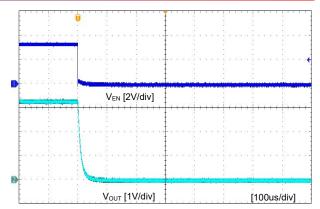


Figure 11. Turn-Off Response, GLF1501 $V_{IN} = 3.3 \text{ V}$, $C_{OUT} = 0.1 \text{ uF}$, $R_L = 150 \Omega$

APPLICATION INFORMATION

The GLF1501 is a fully integrated 3 A NMOS load switch with fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 0.85 V to 3.6 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current, avoiding unwanted standby current from the input power supply.

Input Capacitor

A capacitor is recommended to be placed close to the V_{IN} pin to reduce the voltage drop on the input power rail caused by transient inrush current at start-up. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

An output capacitor is recommended to minimize voltage undershoot on the output pin during the transition when the switch is turned off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The C_{OUT} capacitor should be placed close to the VOUT and GND pins.

Reverse Current Blocking

The GLF1501 has a built-in reverse current blocking protection. When the device is disabled, the reverse current blocking protection is activated to prevent the reverse current from the Vout to the Vin source.

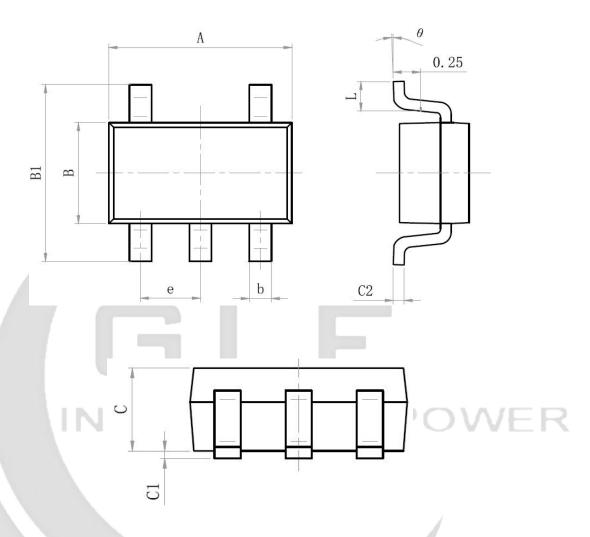
EN pin

The GLF1501 can be activated by EN pin high signal. Note that the EN pin has an internal pull-down resistor to maintain a reliable status without EN signal applied from an external controller.

Board Layout

All traces should be as short as possible to minimize parasitic inductance effect. Wide traces for VIN, VOUT, and GND will help reduce signal degradation and parasitic effects during dynamic operations as well as improve the thermal performance at high load current.

PACKAGE OUTLINE



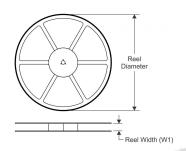
Size	Min(mm)	Max(mm)	Size Mark	Min(mm)	Max(mm)
A	2.82	3.02	C	1.05	1. 15
е	0.9	95 (BSC)	C1	0.03	0.15
b	0.28	0.45	C2	0.12	0. 23
В	1.50	1. 70	L	0.35	0.55
B1	2.60	3.00	θ	0°	8°

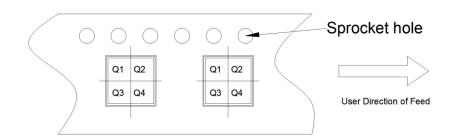


TAPE AND REEL INFORMATION

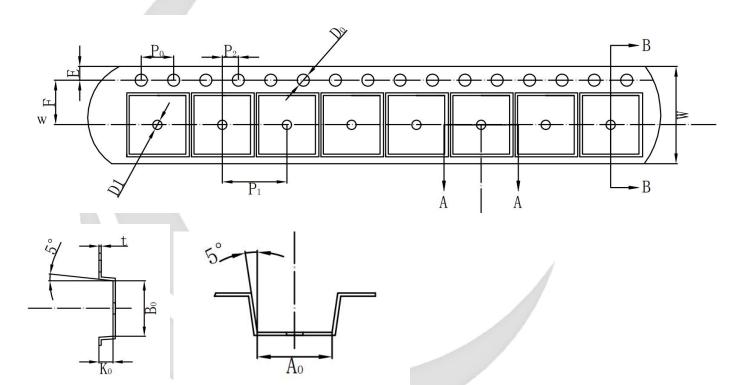
REEL DIMENSIONS

QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE





TAPE DIMENSIONS



Device	Package	Pins	SPQ	Reel Diameter (mm)	Reel Width W1	A0	В0	K0	P1	W	Pin1
GLF1501-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3

Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P1: Pitch between successive cavity centers



SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

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